

FORM PTO-1449 <u>LIST OF DOCUMENTS CITED BY APPLICANT</u>				Atty. Docket No. XA-9693A	Appn. No. 10/701,497		
				Applicant Yoshitaka SASAGO et al.			
				Filing Date HEREWITH	Group 11-06-03		1800
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
JM	AA	5,095,344	03/10/92	Harari (corrs. to JP 2694618)	357	23.5	
JM	AB	5,739,569	4/98	Chen	257	322	
JM	AC	5,773,863	6/98	Burr et al.	257	316	
JM	AD	6,492,690	12/02	Ueno et al.	257	316	
JM	AE	4,561,004	12/85	Kuo et al.	257	319	
JM	AF	4,745,083	5/88	Huie	257	316	
JM	AG	5,455,792	10/95	Yi	257	345	
JM	AH	5,640,032	6/97	Tomioka	257	316	
	AI						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
AJ		2694618	09/12/97	Japan			No-
AK		9-321157	12/12/97	Japan			Abstract
AL							
AM							
AN							
AO							
OTHER (including author, title, date, pertinent pages, etc.)							
AP		"Ohyo Butsuri" (or APPLIED PHYSICS), The Japan Society of Applied Physics, Vol. 65, No. 11, November 10, 1996, pp. 1114-1124.					
AQ		K. Naruko et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select Gate on its Source Side", IEDM, 1999, pp. 603-606.					
AR							
Examiner				Date Considered 12-01-05			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							

FORM PTO-1449				Atty. Docket No.	Appln. No.		
<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>				XA-9693A	10/701,497		
				Applicant			
				Yoshitaka SASAGO et al.			
				Filing Date	Group		
				HEREWITH 11-06-03	2822		
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA	5,095,344	03/10/92	Harari (corrs. to JP 2694618)	257	23.5	
	AB	5,739,569	4/98	Chen	257	322	
	AC	5,773,863	6/98	Burr et al.	257	316	
	AD	6,492,690	12/02	Ueno et al.	257	316	
	AE	4,561,004	12/85	Kuo et al.	257	319	
	AF	4,745,083	5/88	Hsieh	257	316	
	AG	5,455,792	10/95	Xi	257	945	
	AH	5,640,032	6/97	Tomioka	257	316	
	AI						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
JMJ	AJ	2694618	09/12/97	Japan			No
JMJ	AK	9-321157	12/12/97	Japan			Abstract
	AL						
	AM						
	AN						
	AO						
OTHER (including author, title, date, pertinent pages, etc.)							
	AP	"Ohyo Butsuri" (or APPLIED PHYSICS), The Japan Society of Applied Physics, Vol. 65, No. 11, November 10, 1996, pp. 1114-1124.					
JMJ	AQ	K. Naruke et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select-Gate on its Source Side", IEDM, 1989, pp. 603-606.					
	AR						
Examiner	J. M. Thomas			Date Considered 07-07-06			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							